



RLT6405G TECHNICAL DATA

Short Wavelength Laserdiode

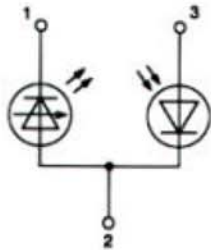
Structure: **AlGaInP**, index guided

Lasing wavelength: **640 nm**

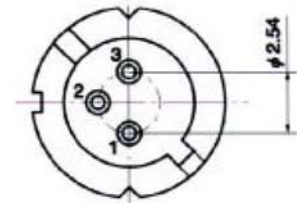
Max. optical power: **5 mW**

Package: **9 mm**

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	5	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operation Case Temperature	T _C	-10 .. +40	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	kink free			5	mW
Threshold Current	I _{th}		35	45	55	mA
Operation Current	I _{op}	P _o =5mW	45	55	70	mA
Operating Voltage	V _{op}	P _o =5mW	2.0	2.4		V
Lasing Wavelength	λ _p	P _o =5mW		640	645	nm
Beam Divergence	θ _∥	P _o =5mW	8	10	11	°
Beam Divergence	θ _⊥	P _o =5mW	25	31	40	°
Monitor Current	I _m	P _o =5mW, V _r =5V	5	10	20	μA
Slope Efficiency	η	mW/mA	0.1	0.3	0.5	
Astigmatism	A _s	P _o =5mW		11		μm